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Haren eng-Mars 9/8/03 (Signature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of : September 08, 2003

Khater et al. : Group Art Unit:

Serial No. 10/604,988 : Examiner: Steven Post

Filed: August 29, 2003 : International Business Machines Corporation

2070 Route 52

Hopewell Junction, NY 12533

TITLE: BIOPOLAR TRANSISTOR HAVING RAISED EXTRINSIC BASE WITH SELECTABLE SELF-ALIGNMENT AND METHDOS OF FORMING SAME

INFORMATION DISCLOSURE STATEMENT

COMMISSIONER FOR PATENTS P.O. BOX 1450 ALEXANDRIA, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,

KHATER et al.

Tiffany L. Townsend, Attorney

Registration/No. 43,199

Telephoné No. 845-894-3668

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		IEEE Electron Device I and 207 GHz fT in a M	Letters, Vol. 23, No. 5 anufacturable Techn	5, May 2002, "Self-Aligned SiCology", Jagannathan et al., pp.	Ge NPN Transist . 258 - 260.	tors With 285	GHz FMAX		
		IEEE International Electron Device Meeting Technical Digest, 771 (2002), "SiGe HBTs with Cut-off Frequency of 350 Ghz,"							
		Rieh et al., pp. 1-4.							
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